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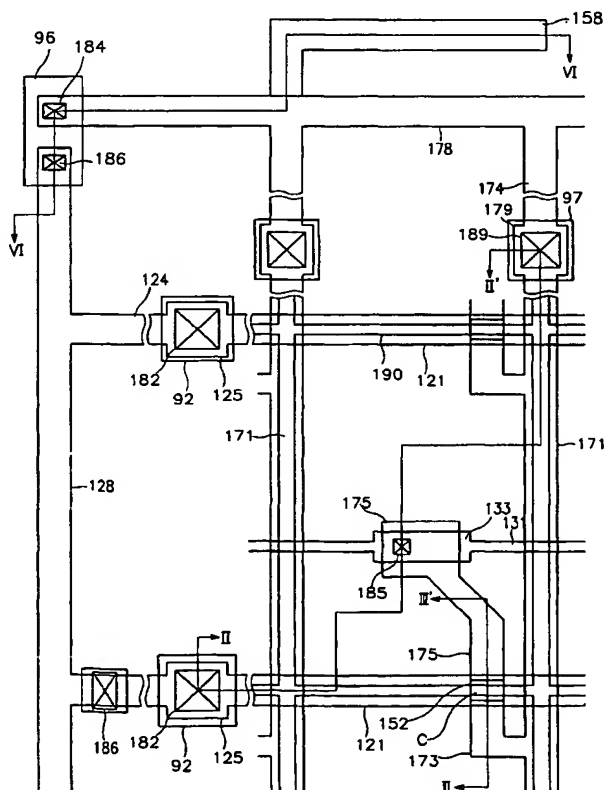
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(54) Title: A THIN FILM TRANSLATOR ARRAY PANEL AND A METHOD FOR MANUFACTURING THE PANEL



(57) Abstract: A gate wire including a gate line and a gate electrode is formed on a substrate and a gate insulating layer is formed on the substrate. A semiconductor pattern and an etching assistant pattern are formed on the gate insulating layer and a source/drain conductor pattern and an etching assistant layer are formed on the semiconductor pattern and the etching assistant pattern. A data wire including a data line and source and drain electrodes separated from each other is formed by removing the etching assistant layer and partly removing the source/drain conductor pattern. A pixel electrode connected to the drain electrodes is formed.

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